

Amendments to the Claims



1. (Currently Amended): Silicon-on-insulator comprising integrated circuitry, comprising:

a substrate comprising an insulator layer of silicon-on-insulator circuitry, the insulator layer comprising silicon dioxide;

a semiconductive silicon comprising layer of the silicon-on-insulator circuitry, the silicon comprising layer being received ~~proximate~~ on the insulator layer, the silicon comprising layer comprising a pair of source/drain regions formed therein and a channel region formed therein which is received intermediate the source/drain regions;

a transistor gate received operably proximate the channel region; and

the insulator layer comprising a silicon nitride comprising region received intermediate the silicon dioxide comprising layer and the source/drain regions and running along ~~at least~~ only a portion of the channel region between the source/drain regions.

2. (Canceled)

3. (Canceled).

4. (Currently Amended): The circuitry of claim 1 wherein the ~~silicon comprising layer contacts the insulator layer, and~~ the source/drain regions extend to the insulator layer.

5. (Canceled).

6. (Original): The circuitry of claim 1 wherein the silicon nitride comprising region has a thickness of from about 10 Angstroms to about 50 Angstroms.

7. (Currently Amended): Silicon-on-insulator comprising integrated circuitry, comprising:

a substrate comprising an insulator layer of silicon-on-insulator circuitry, the insulator layer comprising silicon dioxide;

a semiconductive silicon comprising layer of the silicon-on-insulator circuitry, the silicon comprising layer being received on the insulator layer, the silicon comprising layer comprising a pair of source/drain regions formed therein and extending to the insulator layer, the silicon comprising layer comprising a partially depleted channel region formed therein which is received intermediate the source/drain regions;

a transistor gate received operably proximate the channel region; and

the insulator layer comprising a silicon nitride comprising region received intermediate the silicon dioxide comprising layer and the source/drain regions and running along ~~at least~~ only a portion of the channel region between the source/drain regions.

8. (Canceled).

9. (Canceled).

10. (Original): The circuitry of claim 7 wherein the silicon nitride comprising region has a thickness of from about 10 Angstroms to about 50 Angstroms.

11. (Withdrawn): Silicon-on-insulator comprising integrated circuitry, comprising:

a substrate comprising a semiconductive silicon comprising layer of silicon-on-insulator circuitry, the silicon comprising layer comprising a pair of source/drain regions formed therein and a channel region formed therein which is received intermediate the source/drain regions;

a transistor gate received operably proximate the channel region; and

an insulator layer of the silicon-on-insulator circuitry received on the silicon comprising layer, the insulator layer comprising a first silicon dioxide comprising region in contact with the silicon comprising layer and running along at least a portion of the channel region between the source/drain regions, a silicon nitride comprising region in contact with the first silicon dioxide comprising region and running along at least a portion of the channel region, and a second silicon dioxide comprising region in contact with the silicon nitride comprising region, the silicon nitride comprising region being received intermediate the first and second silicon dioxide comprising regions.

12. (Withdrawn): The circuitry of claim 11 wherein the silicon nitride comprising region runs along only a portion of the channel region between the source/drain regions.

13. (Withdrawn): The circuitry of claim 11 wherein the silicon nitride comprising region runs entirely along the channel region between the source/drain regions.

14. (Withdrawn): The circuitry of claim 11 wherein the silicon nitride comprising region has a thickness of from about 10 Angstroms to about 50 Angstroms.

15. (Withdrawn): The circuitry of claim 11 wherein the first silicon dioxide comprising region has a thickness of from about 10 Angstroms to about 30 Angstroms.

16. (Withdrawn): The circuitry of claim 11 wherein the source/drain regions extend to the insulator layer.

Claims 17-61 (Cancelled).

62. (New): The circuitry of claim 1 wherein the silicon nitride comprising region contacts the silicon comprising layer.

63. (New): The circuitry of claim 1 wherein the portion of the silicon nitride comprising region is discontinuous relative to the channel region.

64. (New): The circuitry of claim 1 wherein the portion of the silicon nitride comprising region is continuous relative to the channel region.

65. (New): The circuitry of claim 1 wherein the channel region comprises a central region laterally centered between the source/drain regions, the portion of the silicon nitride comprising region being laterally spaced from said central region.

66. (New): The circuitry of claim 65 wherein the silicon nitride comprising region contacts the silicon comprising layer.

67. (New): The circuitry of claim 1 wherein the channel region comprises a central region laterally centered between the source/drain regions, the portion of the silicon nitride comprising region running along said central region.

68. (New): The circuitry of claim 67 wherein the silicon nitride comprising region contacts the silicon comprising layer.

69. (New): The circuitry of claim 7 wherein the portion of the silicon nitride comprising region is discontinuous relative to the channel region.

70. (New): The circuitry of claim 7 wherein the portion of the silicon nitride comprising region is continuous relative to the channel region.

71. (New): The circuitry of claim 7 wherein the channel region comprises a central region laterally centered between the source/drain regions, the portion of the silicon nitride comprising region being laterally spaced from said central region.

72. (New): The circuitry of claim 7 wherein the channel region comprises a central region laterally centered between the source/drain regions, the portion of the silicon nitride comprising region running along said central region.